

# 2SB1722G

## Silicon PNP epitaxial planar type

For high breakdown voltage low-frequency amplification

### ■ Features

- High collector-emitter voltage (Base open)  $V_{CEO}$
- SS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	-100	V
Collector-emitter voltage (Base open)	$V_{CEO}$	-100	V
Emitter-base voltage (Collector open)	$V_{EBO}$	-5	V
Collector current	$I_C$	-20	mA
Peak collector current	$I_{CP}$	-50	mA
Collector power dissipation	$P_C$	125	mW
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

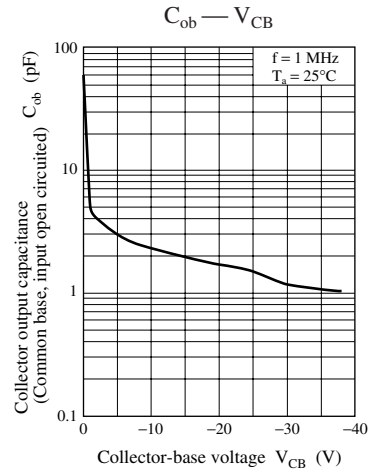
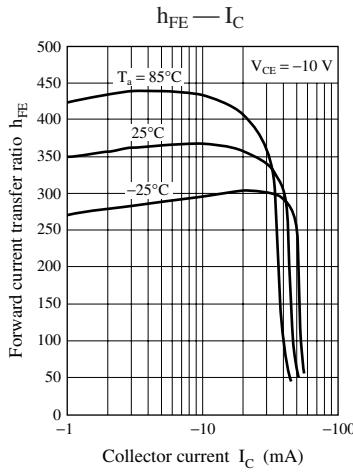
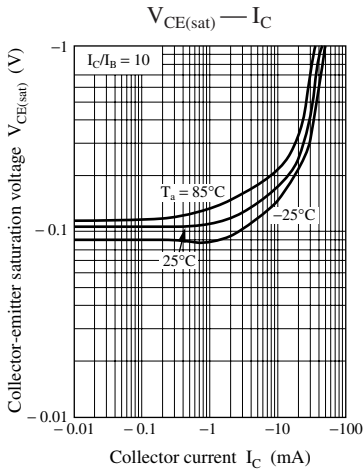
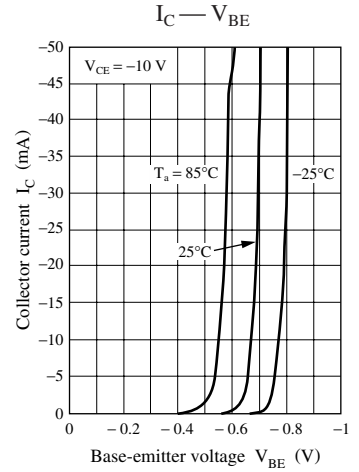
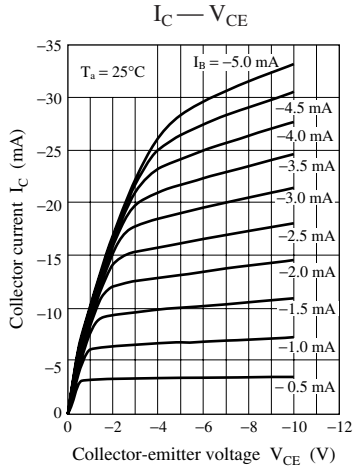
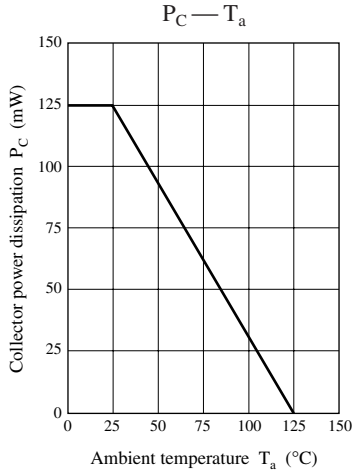
### ■ Package

- Code  
SSMini3-F3
- Marking Symbol: 4R
- Pin Name
  1. Base
  2. Emitter
  3. Collector

### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

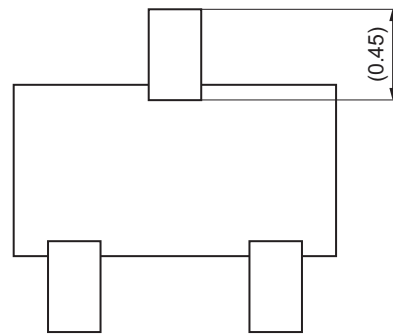
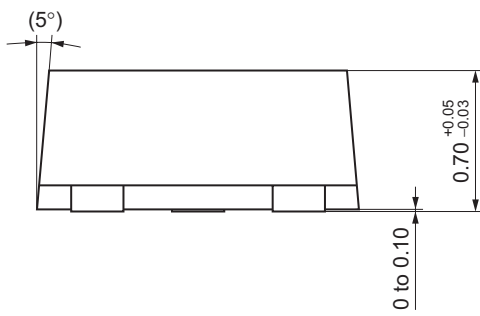
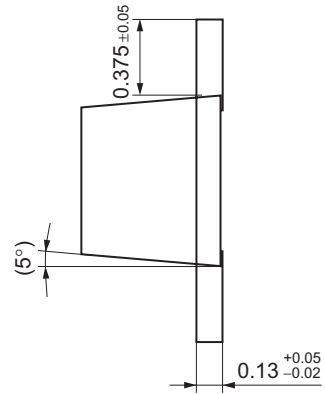
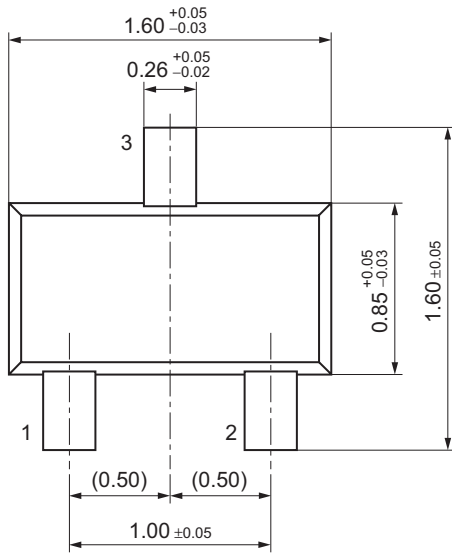
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = -10 \mu\text{A}$ , $I_E = 0$	-100			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = -1 \text{ mA}$ , $I_B = 0$	-100			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = -10 \mu\text{A}$ , $I_C = 0$	-5			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -50 \text{ V}$ , $I_E = 0$			-100	nA
Collector-emitter cut-off current (Base open)	$I_{CEO}$	$V_{CE} = -50 \text{ V}$ , $I_B = 0$			-1	$\mu\text{A}$
Forward current transfer ratio	$h_{FE}$	$V_{CE} = -10 \text{ V}$ , $I_C = -2 \text{ mA}$	200		700	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10 \text{ mA}$ , $I_B = -1 \text{ mA}$			-0.3	V
Transition frequency	$f_T$	$V_{CB} = -5 \text{ V}$ , $I_E = 2 \text{ mA}$ , $f = 200 \text{ MHz}$		200		MHz

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



SSMini3-F3

Unit: mm



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